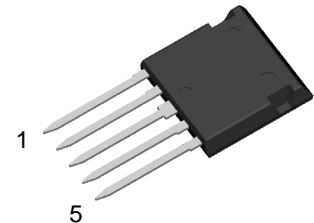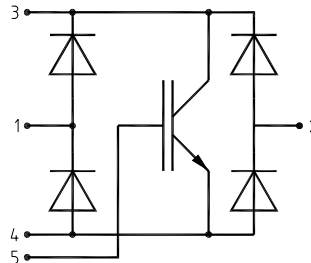# Bidirectional Switch with IGBT and fast Diode Bridge

in ISOPLUS i4-PAC™

FIO 50-12BD

I_{C25} = 50 A
V_{CES} = 1200 V
$V_{CE(sat)\,typ.}$ = 2.0 V

IGBT

Symbol	Conditions	Maximum Ratings	
V_{CES}	T_{VJ} = 25°C to 150°C	1200	V
V_{GES}		± 20	V
I_{C25}	T_C = 25°C	50	A
I_{C90}	T_C = 90°C	32	A
I_{CM}	V_{GE} = ±15 V; R_G = 39 Ω; T_{VJ} = 125°C	50	A
V_{CEK}	RBSOA, Clamped inductive load; L = 100 µH	V_{CES}	
t_{SC} (SCSOA)	V_{CE} = 900V; V_{GE} = ±15 V; R_G = 39 Ω; T_{VJ} = 125°C non-repetitive	10	µs
P_{tot}	T_C = 25°C	200	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	I_C = 30 A; V_{GE} = 15 V; T_{VJ} = 25°C		2.0	2.6	V
	T_{VJ} = 125°C		2.3		V
$V_{GE(th)}$	I_C = 1 mA; V_{GE} = V_{CE}	4.5		6.5	V
I_{CES}	V_{CE} = V_{CES}; V_{GE} = 0 V; T_{VJ} = 25°C			0.4	mA
	T_{VJ} = 125°C		0.4		mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V			200	nA
$t_{d(on)}$			150		ns
t_r	Inductive load, T_{VJ} = 125°C		60		ns
$t_{d(off)}$	V_{CE} = 600 V; I_C = 30 A		700		ns
t_f	V_{GE} = ±15 V; R_G = 39 Ω		50		ns
E_{on}			3.6		mJ
E_{off}			3.0		mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz		2		nF
Q_{Gon}	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 30 A		250		nC
R_{thJC}				0.6	K/W
R_{thJS}			1.2		K/W

Features

- IGBT
  - low saturation voltage
  - positive temperature coefficient for easy paralleling
  - fast switching
  - short tail current for optimized performance in resonant circuits
- HiPerFRED™ diodes
  - fast reverse recovery
  - low operating forward voltage
  - low leakage current
- ISOPLUS i4-PAC™ package
  - isolated back surface
  - low coupling capacity between pins and heatsink
  - enlarged creepage towards heatsink
  - application friendly pinout
  - low inductive current path
  - high reliability
  - industry standard outline

Applications

switches to control bidirectional current flow by a single control signal:
- matrix converters
- spare matrix converters
- AC controllers

IXYS

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25°C$	48	A
I_{F90}	$T_C = 90°C$	25	A

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V_F	$I_F = 30$ A; $T_{VJ} = 25°C$		2.4	2.8	V
	$T_{VJ} = 125°C$		1.8		V
I_{RM}	$I_F = 30$ A; $di_F/dt = -500$ A/µs; $T_{VJ} = 125°C$		27		A
t_{rr}	$V_R = 600$ V; $V_{GE} = 0$ V		150		ns
R_{thJC}	(per diode)			1.3	K/W
R_{thJS}			2.6		K/W

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+150	°C
T_{stg}		-55...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1$ mA; 50/60 Hz	2500	V~
F_C	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
C_p	coupling capacity between shorted pins and mounting tab in the case		40		pF
d_S, d_A	pin - pin	1.7			mm
d_S, d_A	pin - backside metal	5.5			mm
Weight			9		g

Dimensions in mm (1 mm = 0.0394")